

Nano-sized Laser Beams without Diffraction Spreading

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ABSTRACT

Whereas exciting progress has been made to beat diffraction in optical spectroscopy [1-8], making a nano-sized laser beam remains challenging due to diffraction spread [9,10]. Using Bethe's expression for the optical transmission coefficient of a circular hole in a perfect conductor screen of zero thickness [9,11]. $T=1024\pi^3a^6/27\lambda^4$, we found that the transmission of light with a wavelength $\lambda=800$ nm through such a circular hole of a radius of 1 nm is about $\sim 2.3 \times 10^{-6}$. So a decent nanosized laser beam for miniaturization of optical elements is not available. Here we show that coupling Surface Plasmon-Polaritons (SPPs) to appropriate dielectric material can result in fundamentally diffraction-free down-sized, especially nano-sized laser beams. For example, the composite structure $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/(\text{SiO}_2, \text{Si}_3\text{N}_4, \text{SiO}_2)$ can achieve a nano-sized laser beam of about half the incoming light intensity. This approach, by transforming the macroscopic laser beams into multiple nano-sized laser beams, holds promise for ultrafast laser imprinting of nanopores for DNA sequencing and other miniature photonic devices in optical signal processing industries.

KEYWORDS

Optical spectroscopy, Nano-sized Laser Beams, DNA sequencing

INTRODUCTION

In optics, diffraction renders a blurred Airy disk image for a point object and thus creates a resolution limit to an imaging instrument [1]. Over the past decades, tremendous progress has been made to improve the resolutions of optical images. Hell et al. used a depletion laser beam to squeeze the non-depleted excitation fluorescent spot to a tiny point and achieved a 35 nm resolution of molecule images [2,3]. Zhuang et al. reconstructed 20 nm-resolution images of individual photo-switchable fluorescent molecules that are turned on and off by excitation light of different colors [12]. Betzig et al. used photo-activated localization microscopy to image intracellular proteins at a nanometer resolution [5]. Pendry proposed to use survived evanescent waves in negative-index media to make a perfect image [6], which was realized experimentally by Zhang et al., [7]. Yablouovitch et al. developed a 3D tapered metal-insulator-metal nano-gaped device that delivers background-free near-field images with a deep sub-wavelength resolution.

While these landmark advances are impressive in beating diffraction in image optics, overcoming the diffraction spreading of a laser beam is rarely studied. Light from a sub-wavelength aperture usually diffracts in all directions, which makes a nano-sized laser beam virtually impossible [9]. Townes et al. first discussed the possible suppression of rapid diffraction-spreading of a laser beam in nonlinear dielectric media by an intense laser [10]. Lezec et al. created an almost-directional light beam out of metallic films of a bull's eye structure, whose practical application is limited by the complicated fabrication of periodic grooves [13]. Noticing the importance of beating diffraction in science [1-8], here we propose an approach to make a nano-sized laser beam for technological applications

TRANSFER MATRIX MODELLING

We use a planar metal-dielectric tri-layer film to absorb laser light as SPPs at a conductor/dielectric interface [14,15] and add another top dielectric layer to reduce SPPs to free-space optical waves. This conversion does allow photons traveling directionally without diffraction [16].

We calculate the intensity of light reflected by and transmitted through this coupling structure [17-21] with a transfer-matrix method. The transfer-matrix method is briefly summarized as follows. Suppose the coupling structures are composed of optically isotropic and

homogeneous N planar layers. Each layer i has a thickness d_i . Both the width of the first layer and that of the last layer are assumed to be infinite. The dielectric properties of each layer i are characterized by its complex dielectric functions $\epsilon_i(\omega)$.

We use the dielectric functions calculated from the refractive index of materials (<https://www.filmetrics.com/refractive-index-database>). A p-polarized monochromatic plane wave with wavelength λ_0 is incident on the stack from layer 1 through layer N, making an arbitrary angle of incidence θ_1 with respect to the surface normal of the first interface. We describe the electric field in layer i as a superposition of the reflected and transmitted plane waves. For example, for a single ideal interface at the O-xy plane, the electric field below and above this interface is written as $E(x, z < 0) = Ee^{i(k_{1x}x + k_{1z}z - \omega t)} + E'e^{i(k_{1x}x - k_{1z}z - \omega t)}$ and $E(x, z > 0) = Ee^{i(k_{2x}x + k_{2z}z - \omega t)} + E'e^{i(k_{2x}x - k_{2z}z - \omega t)}$. Here the wave-vector for the incident plane wave is $k_{1x}\mathbf{i} + k_{1z}\mathbf{k}$, the wave-vector for the reflected plane wave is $k_{1x}\mathbf{i} + k_{1z}\mathbf{k}$ in layer 1, and so on for the wave-vectors in layer 2. The x-components of all the wave-vectors are equal, i.e., $k_{1x} = k_{2x} = \dots = k_{Nx} = 2\pi n_1 \sin\theta_1 / \lambda_0$. The z-components of the wave-vectors can be written as $k_{iz} = 2\pi\sqrt{\epsilon_i - \epsilon_1 \sin^2\theta_1} / \lambda_0$. The transformation of the incident and reflected fields across each interface i of two neighboring i-th and (i+1)-th layers are related to each other by an interface transfer matrix T(i), i.e.,

$$\begin{bmatrix} E_{(i+1)x} \\ E'_{(i+1)x} \end{bmatrix} = T(i) \begin{bmatrix} E_{ix} \\ E'_{ix} \end{bmatrix} \text{ with } T(i) = \frac{1}{2} \begin{bmatrix} 1 + \frac{\epsilon_i k_{(i+1)z}}{\epsilon_{(i+1)} k_{iz}} & 1 - \frac{\epsilon_i k_{(i+1)z}}{\epsilon_{(i+1)} k_{iz}} \\ 1 - \frac{\epsilon_i k_{(i+1)z}}{\epsilon_{(i+1)} k_{iz}} & 1 + \frac{\epsilon_i k_{(i+1)z}}{\epsilon_{(i+1)} k_{iz}} \end{bmatrix} \quad (1)$$

Similarly, when the optical fields travel in a single j-th layer of thickness d_j , the field amplitudes in the upper- and down-sides of this layer are related by a propagation transfer matrix T(d_j), i.e.

$$\begin{bmatrix} E_{jx}(z_j = d_j + z_{j-1}) \\ E'_{jx}(z_j = d_j + z_{j-1}) \end{bmatrix} = T(d_j) \begin{bmatrix} E_{jx}(z_j = z_{j-1}) \\ E'_{jx}(z_j = z_{j-1}) \end{bmatrix}, \text{ with } T(d_j) = \begin{bmatrix} e^{ik_{2z}d_j} & 0 \\ 0 & e^{-ik_{2z}d_j} \end{bmatrix} e^{ik_{2x}d_j \tan\theta_2} \quad (2)$$

For a multilayer film, the electric fields at the first interface are related to those at the last interface by an overall T-matrix, which is the successive matrix products of the propagation transfer matrix and interface transfer matrix, i.e.,

$$\begin{bmatrix} E_{N-1x}(z_{N-1} = d_{N-1} + z_{N-2}) \\ E'_{N-1x}(z_{N-1} = d_{N-1} + z_{N-2}) \end{bmatrix} = T_{total} \begin{bmatrix} E_{1x}(z_1 = 0) \\ E'_{1x}(z_1 = 0) \end{bmatrix},$$

Where,

$$T_{total} = T(N-1)T(d_{N-1}) \dots T(3)T(d_3)T(2)T(d_2)T(1). \quad (3)$$

If we set the incident and reflected electric field from the bottom-most layer as one and $r = E'1 / E1$ and the transmitted and reflected field from the top-most layer as $t = EN/E1$ and 0, the matrix relation can then be expressed as:

$$\begin{bmatrix} t \cos\theta_N \\ 0 \end{bmatrix} = \begin{bmatrix} T_{11} & T_{12} \\ T_{21} & T_{22} \end{bmatrix} \begin{bmatrix} \cos\theta_1 \\ r \cos\theta_1 \end{bmatrix} \quad (4)$$

Thus the transmission and reflection coefficients of the final layer are given by

$$t = (T_{11} - T_{12}T_{21} / T_{22}) \cos\theta_1 / \cos\theta_N \quad (5)$$

and

$$r = -T_{21} / T_{22} \quad (6)$$

Finally, the reflectance R, the transmittance T, and the absorbance A are then given by $R = |r|^2$,

$$T = \text{Re} \left\{ \frac{n_N \cos\theta_N}{n_i \cos\theta_i} \right\} |t|^2 \text{ and } A = 1 - R - T$$

REFLECTANCE AND TRANSMITTANCE OF METAL-DIELECTRIC FILMS

We use this transfer matrix method to design our material structure. At first, we use a tri-layered film $\text{Si}_3\text{N}_4/\text{Au}/\text{SiO}_2$ stack to absorb laser light into SPPs with Kretschmann prism coupling configuration [22]. As shown in Figure 1, the 800 nm wavelength laser light with an angle of incidence is 49.1° is completely trapped at the interface of this film if the thickness of the smooth gold film [23] is about 44.5 nm.

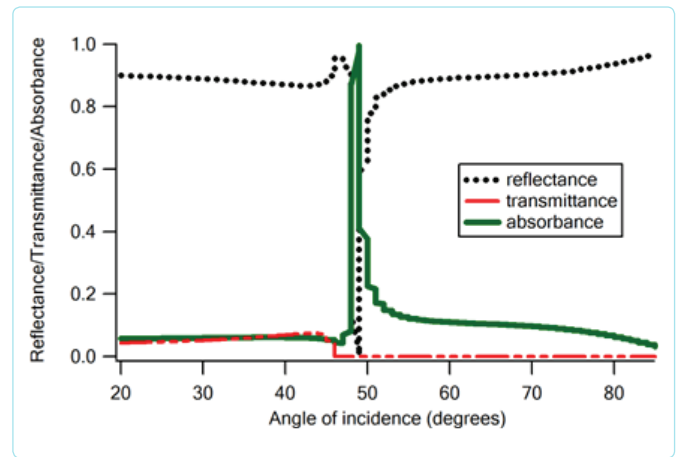


Figure 1: The reflectance, transmittance, and absorbance of the film $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2$ stack vs the angle of incidence. The p-polarized monochromatic light with wavelength 800 nm casts on the film. The surface Plasmon resonance angle is found to be $\theta_{\text{SPP}} = 49.1^\circ$.

We then put another Si_3N_4 layer onto the $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2$ film with varying SiO_2 thickness. As shown in Figure 2, the transmittance of the film $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2/\text{Si}_3\text{N}_4$ is 0~45.8% when the same light incident on it with the same angle of incidence. SPPs can couple efficiently with Si_3N_4 with a maximum transmittance of 45.8% in the sample $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/\text{Si}_3\text{N}_4$.

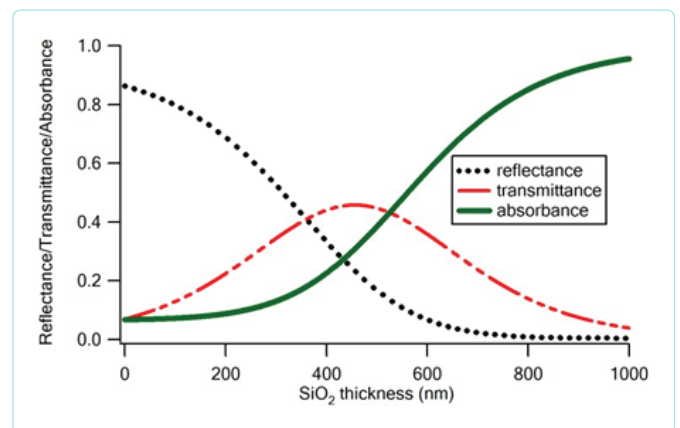


Figure 2: The reflectance, transmittance, and absorbance of $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2/\text{Si}_3\text{N}_4$ film vs SiO_2 thickness. When p-polarized wavelength 800 nm light with casts on the sample $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/\text{Si}_3\text{N}_4$ with an angle of incidence is $\theta_{\text{SPP}} = 49.1^\circ$, the maximum transmittance is about 45.8%.

To understand the physics for this optical transmission, we also

calculate the magnetic field in the i -th layer of the sample $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/\text{Si}_3\text{N}_4$, which takes the following form.

$$H_{y_i} = \omega \varepsilon_i (E_{ix} - E'_{ix}) / k_{iz} \quad (9)$$

Here the x -components of the electric fields, including both the incident electric fields and the reflected electric fields in each layer, are also calculated by the transfer matrix formulation (3-6). As shown in Figure 3, the magnetic field amplitude reaches a maximum at the Au/SiO_2 interface and decays exponentially in the SiO_2 layer as plasma-polaritons. When entering the $\text{SiO}_2/\text{Si}_3\text{N}_4$ interface, the magnetic field stops declining and starts to travel through the Si_3N_4 layer as an un-attenuated oscillation. The $\text{SiO}_2/\text{Si}_3\text{N}_4$ interface acts as an excitation source for this un-attenuated oscillation. This interface behaves just like shaking one end of a rope to generate a transverse string wave in the entire rope. This emission of light is self-directional, i.e., is diffraction-free, and is quite different from surface plasmon-coupled emission [24], or direction-selective emission in the metal-dielectric-metal structure [25] or light-beaming caused by the interaction of SPPs with surface grooves in the metal [13], or perfect transmission of light through pinholes in a Fabry-Perot cavity [26]. The top dielectric layer acts as a vent for SPP photons to emit, and the more surface area of the dielectric, the more free photons one can get.

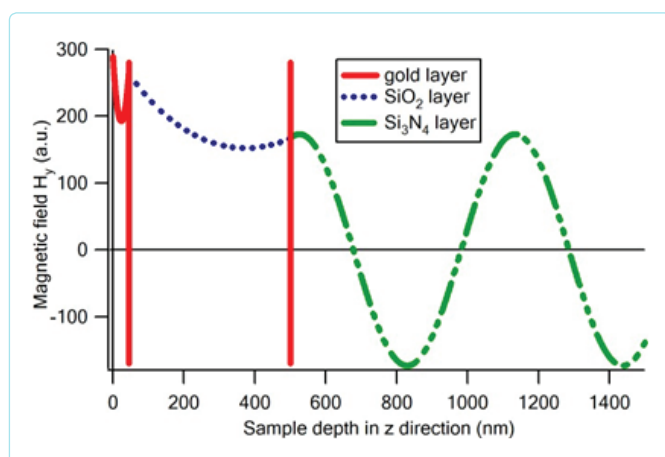


Figure 3: The magnetic field H_y in the sample $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/\text{Si}_3\text{N}_4$ vs. sample depth. The magnetic field amplitude reaches the maximum at the Au/SiO_2 interface and then decays exponentially in the SiO_2 layer to form plasma polarities. When entering the $\text{SiO}_2/\text{Si}_3\text{N}_4$ interface, the magnetic field in the SiO_2 stops declining and starts to travel through the Si_3N_4 layer as un-attenuated oscillations.

This dielectric/metal/dielectric/dielectric structure can modify the wave-fronts of electromagnetic waves by the top dielectric material to turn laser light on and off simultaneously. For example, composite structure $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/(\text{SiO}_2, \text{Si}_3\text{N}_4, \text{SiO}_2)$ is obtained by sideways connecting the SPP structure $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2$ with the coupling structure $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/\text{Si}_3\text{N}_4$, as shown in Figure 4. This composite structure can trap most SPP photons at the gold-silicon interface, and a certain amount of SPPs becomes propagating photons in the capping layer Si_3N_4 . Since SPPs scatter along with the interface when entering the lateral $\text{Si}_3\text{N}_4/\text{SiO}_2$ boundary, this SPP-scattering does not affect the far-field emission at all [27]. Therefore the beam size of this light transmission depends solely on the contact surface area of the resultant laser beam is the contact area of the topping dielectric material multiplied by a factor of $\sin\theta_1$. So this structure is expected to make an optical beam of a few nanometers with no diffraction spreading. For example, if the contact area of the coupling layer Si_3N_4 is a few nanometers square and the thickness of SPP hosting layer SiO_2 is 456 nm thick, the incident laser could become a nano-sized laser beam with a tremendous transmittance of 45.8%.

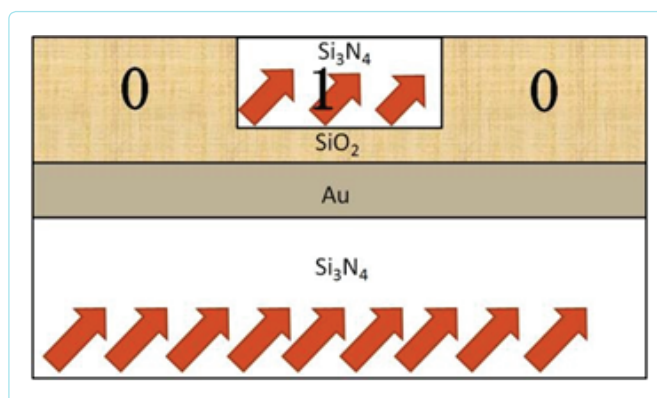


Figure 4: The light is partially turned on and off in the composite structure $\text{Si}_3\text{N}_4/\text{Au}(44.5\text{nm})/\text{SiO}_2(456\text{nm})/(\text{SiO}_2, \text{Si}_3\text{N}_4, \text{SiO}_2)$. The beam size of this dielectric-coupled SPP emission depends solely on the contact area of the top dielectric coupling layer Si_3N_4 , which turns the light on (hence it stores a bit "1")

CONCLUSIONS

In summary, we performed a systematic study of the optical properties of SPP nanostructures coupled with dielectric materials. While this study has not been experimentally realized, there is no theoretical obstacle to build a diffraction-free laser beam by coupling SPP nanostructures with appropriate dielectric material. The capping layer alignment shows significant flexibility in building structures of interest in a variety of applications. The generation of multiple beams from a single laser source could be used to design new optical storage for fast batch-bit access in big-data industries, or to develop new 3D-printing technology to fabricate nano-porous membranes or nanofibers for efficient industrial-scale hydrogen generation [28] and CO_2 electrolysis for global dioxide emission reduction [29-31]. The merit of this diffraction suppression is that a decent nano-sized laser beam could be made possible. A continuous effort aiming at improving the optical field [32,33] of this sub-wavelength laser beam for the fabrication of a solid-state nanopore for DNA sequencing [34-37] is also possible.

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